

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
9 June 2005 (09.06.2005)

PCT

(10) International Publication Number  
**WO 2005/052893 A1**

(51) International Patent Classification<sup>7</sup>: **G09F 9/00**,  
H05B 33/10, G02F 1/1333

Yuugo [JP/JP]; c/o SEMICONDUCTOR ENERGY LAB-  
ORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,  
2430036 (JP).

(21) International Application Number:  
PCT/JP2004/017537

(81) Designated States (unless otherwise indicated, for every  
kind of national protection available): AE, AG, AL, AM,  
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,  
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,  
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,  
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,  
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,  
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,  
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,  
ZW.

(22) International Filing Date:  
18 November 2004 (18.11.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
2003-399926 28 November 2003 (28.11.2003) JP

(84) Designated States (unless otherwise indicated, for every  
kind of regional protection available): ARIPO (BW, GH,  
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,  
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),  
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,  
FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE,  
SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,  
GW, ML, MR, NE, SN, TD, TG).

(71) Applicant (for all designated States except US): SEMI-  
CONDUCTOR ENERGY LABORATORY CO., LTD.  
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

(72) Inventors; and

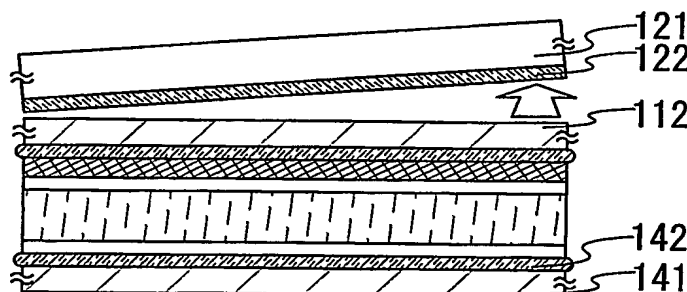
(75) Inventors/Applicants (for US only): YAMASHITA,  
Akio [JP/JP]; c/o SEMICONDUCTOR ENERGY LABO-  
RATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,  
2430036 (JP). FUKUMOTO, Yumiko [JP/JP]; c/o SEMI-  
CONDUCTOR ENERGY LABORATORY CO., LTD.,  
398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP). GOTO,

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guid-  
ance Notes on Codes and Abbreviations" appearing at the begin-  
ning of each regular issue of the PCT Gazette.

(54) Title: METHOD OF MANUFACTURING DISPLAY DEVICE



(57) Abstract: To provide a method of manufacturing  
a display device having an excellent impact resistance  
property with high yield, in particular, a method of  
manufacturing a display device having an optical film  
that is formed using a plastic substrate. The method  
of manufacturing a display device includes the steps  
of: laminating a metal film, an oxide film, and an  
optical filter on a first substrate; separating the optical  
filter from the first substrate; attaching the optical  
filter to a second substrate; forming a layer including  
a pixel on a third substrate; and attaching the layer  
including the pixel to the optical filter.

WO 2005/052893 A1